

Serial No. 09/843,783
Art Unit: 2823

IN THE CLAIMS:

Kindly amend independent claims 1 and 15 to appear as follows, without prejudice:

1. (Twice Amended) A method of reducing film growth rate when growing a carbon- or boron-doped silicon film or silicon-germanium film, comprising:

BZ C1
carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.

15. (Twice Amended) A method of growing a film without sharp pressure transitions, comprising:

BZ C1
carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant

FIS920010024US1

- 2 -